



Dual N-Channel 30 V (D-S) MOSFETs

| PRODUCT SUMMARY | | | | |
|-----------------|---------------------|-----------------------------------|--------------------|-----------------------|
| | V _{DS} (V) | R _{DS(on)} (Ω) (Max.) | I _D (A) | Q _g (Typ.) |
| Channel-1 | 30 | 0.0058 at V _{GS} = 10 V | 40 ^a | 12.5 nC |
| | | 0.0075 at V _{GS} = 4.5 V | 40 ^a | |
| Channel-2 | 30 | 0.0030 at V _{GS} = 10 V | 40 ^a | 29 nC |
| | | 0.0035 at V _{GS} = 4.5 V | 40 ^a | |

FEATURES

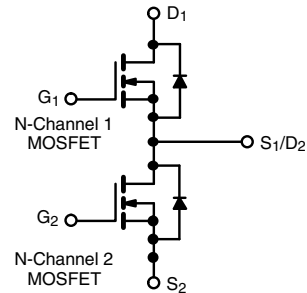
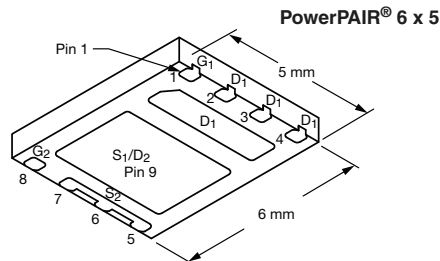
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFETs
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS
 COMPLIANT
 HALOGEN
FREE

APPLICATIONS

- Notebook System Power
- POL
- Synchronous Buck Converter



Ordering Information: SiZ910DT-T1-GE3 (Lead (Pb)-free and Halogen-free)

| ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted) | | | | | |
|---|-----------------------------------|---------------------|---------------------|------|----|
| Parameter | Symbol | Channel-1 | Channel-2 | Unit | |
| Drain-Source Voltage | V _{DS} | 30 | | V | |
| Gate-Source Voltage | V _{GS} | ± 20 | | | |
| Continuous Drain Current (T _J = 150 °C) | I _D | 40 ^a | 40 ^a | A | |
| | | 40 ^a | 40 ^a | | |
| | | 22 ^{b, c} | 32 ^{b, c} | | |
| | | 17 ^{b, c} | 26 ^{b, c} | | |
| Pulsed Drain Current (t = 300 μs) | I _{DM} | 100 | 120 | A | |
| Continuous Source Drain Diode Current | I _S | 24 ^a | 28 ^a | | |
| | | 3.8 ^{b, c} | 4.3 ^{b, c} | | |
| Single Pulse Avalanche Current | L = 0.1 mH | I _{AS} | 25 | 40 | mJ |
| Single Pulse Avalanche Energy | | E _{AS} | 31 | 80 | |
| Maximum Power Dissipation | P _D | 48 | 100 | W | |
| | | 31 | 64 | | |
| | | 4.6 ^{b, c} | 5.2 ^{b, c} | | |
| | | 3 ^{b, c} | 3.3 ^{b, c} | | |
| Operating Junction and Storage Temperature Range | T _J , T _{stg} | - 55 to 150 | | °C | |
| Soldering Recommendations (Peak Temperature) ^{d, e} | | 260 | | | |

| THERMAL RESISTANCE RATINGS | | | | | | | |
|---|--------------|-------------------|------|-----------|------|------|------|
| Parameter | Symbol | Channel-1 | | Channel-2 | | Unit | |
| | | Typ. | Max. | Typ. | Max. | | |
| Maximum Junction-to-Ambient ^{b, f} | t ≤ 10 s | R _{thJA} | 22 | 27 | 19 | 24 | °C/W |
| Maximum Junction-to-Case (Drain) | Steady State | R _{thJC} | 2.1 | 2.6 | 1 | 1.25 | |

Notes:

a. Package limited - T_C = 25 °C.

b. Surface mounted on 1" x 1" FR4 board.

c. t = 10 s.

d. See solder profile (www.vishay.com/doc?73257). The PowerPAIR is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under steady state conditions is 62 °C/W for channel-1 and 55 °C/W for channel-2.

| SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted) | | | | | | | | |
|---|-------------------------|---|--|------|--------|-----------|----------------------|----|
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit | | |
| Static | | | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | Ch-1 | 30 | | | V | |
| | | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | Ch-2 | 30 | | | | |
| V_{DS} Temperature Coefficient | $\Delta V_{DS}/T_J$ | $I_D = 250\text{ }\mu\text{A}$ | Ch-1 | | 33 | | mV/ $^\circ\text{C}$ | |
| | | $I_D = 250\text{ }\mu\text{A}$ | Ch-2 | | 31 | | | |
| $V_{GS(th)}$ Temperature Coefficient | $\Delta V_{GS(th)}/T_J$ | $I_D = 250\text{ }\mu\text{A}$ | Ch-1 | | - 5.4 | | | |
| | | $I_D = 250\text{ }\mu\text{A}$ | Ch-2 | | - 6.1 | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | Ch-1 | 1.2 | | 2.2 | V | |
| | | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | Ch-2 | 1 | | 2.2 | | |
| Gate Source Leakage | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$ | Ch-1 | | | ± 100 | nA | |
| | | | Ch-2 | | | ± 100 | | |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$ | Ch-1 | | | 1 | μA | |
| | | $V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$ | Ch-2 | | | 1 | | |
| | | $V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$ | Ch-1 | | | 5 | | |
| | | $V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$ | Ch-2 | | | 5 | | |
| On-State Drain Current ^b | $I_{D(on)}$ | $V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$ | Ch-1 | 20 | | | A | |
| | | $V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$ | Ch-2 | 25 | | | | |
| Drain-Source On-State Resistance ^b | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}, I_D = 20\text{ A}$ | Ch-1 | | 0.0048 | 0.0058 | Ω | |
| | | $V_{GS} = 10\text{ V}, I_D = 20\text{ A}$ | Ch-2 | | 0.0025 | 0.0030 | | |
| | | $V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$ | Ch-1 | | 0.0060 | 0.0075 | | |
| | | $V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$ | Ch-2 | | 0.0029 | 0.0035 | | |
| Forward Transconductance ^b | g_{fs} | $V_{DS} = 10\text{ V}, I_D = 20\text{ A}$ | Ch-1 | | 94 | | S | |
| | | $V_{DS} = 10\text{ V}, I_D = 20\text{ A}$ | Ch-2 | | 140 | | | |
| Dynamic^a | | | | | | | | |
| Input Capacitance | C_{iss} | Channel-1 $V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ | Ch-1 | | 1500 | | pF | |
| | | | Ch-2 | | 3600 | | | |
| Output Capacitance | C_{oss} | | Channel-2 $V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ | Ch-1 | | 285 | | |
| | | | | Ch-2 | | 660 | | |
| Reverse Transfer Capacitance | C_{rss} | Channel-1 $V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ | | Ch-1 | | 125 | | |
| | | | | Ch-2 | | 305 | | |
| Total Gate Charge | Q_g | | $V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 20\text{ A}$ | Ch-1 | | 26 | 40 | nC |
| | | | | Ch-2 | | 60 | 110 | |
| | | Channel-1 $V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$ | Ch-1 | | 12.5 | 19 | | |
| | | | Ch-2 | | 29 | 51 | | |
| Gate-Source Charge | Q_{gs} | Channel-2 $V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$ | Ch-1 | | 4.7 | | | |
| | | | Ch-2 | | 10 | | | |
| Gate-Drain Charge | Q_{gd} | | Ch-1 | | 4 | | | |
| | | | Ch-2 | | 9.5 | | | |
| Gate Resistance | R_g | $f = 1\text{ MHz}$ | Ch-1 | 0.5 | 2.6 | 5.2 | Ω | |
| | | | Ch-2 | 0.1 | 0.6 | 1.2 | | |

Notes:

- a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.



| SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted) | | | | | | | | |
|--|--------------|---|--|------|------|------|----|----|
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit | | |
| Dynamic^a | | | | | | | | |
| Turn-On Delay Time | $t_{d(on)}$ | Channel-1 $V_{DD} = 15\text{ V}$, $R_L = 1.5\ \Omega$ $I_D \cong 10\text{ A}$, $V_{GEN} = 4.5\text{ V}$, $R_g = 1\ \Omega$ | Ch-1 | | 20 | 40 | ns | |
| | | | Ch-2 | | 30 | 60 | | |
| Rise Time | t_r | | Ch-1 | | 25 | 50 | | |
| | | | Ch-2 | | 35 | 70 | | |
| Turn-Off Delay Time | $t_{d(off)}$ | Channel-2 $V_{DD} = 15\text{ V}$, $R_L = 1.5\ \Omega$ $I_D \cong 10\text{ A}$, $V_{GEN} = 4.5\text{ V}$, $R_g = 1\ \Omega$ | Ch-1 | | 25 | 50 | | |
| | | | Ch-2 | | 35 | 70 | | |
| Fall Time | t_f | | Ch-1 | | 10 | 20 | | |
| | | | Ch-2 | | 12 | 25 | | |
| Turn-On Delay Time | $t_{d(on)}$ | Channel-1 $V_{DD} = 15\text{ V}$, $R_L = 1.5\ \Omega$ $I_D \cong 10\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\ \Omega$ | Ch-1 | | 10 | 20 | | |
| | | | Ch-2 | | 12 | 25 | | |
| Rise Time | t_r | | Ch-1 | | 25 | 25 | | |
| | | | Ch-2 | | 12 | 25 | | |
| Turn-Off Delay Time | $t_{d(off)}$ | Channel-2 $V_{DD} = 15\text{ V}$, $R_L = 1.5\ \Omega$ $I_D \cong 10\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\ \Omega$ | Ch-1 | | 30 | 60 | | |
| | | | Ch-2 | | 35 | 70 | | |
| Fall Time | t_f | | Ch-1 | | 10 | 20 | | |
| | | | Ch-2 | | 10 | 20 | | |
| Drain-Source Body Diode Characteristics | | | | | | | | |
| Continuous Source-Drain Diode Current | I_S | $T_C = 25\text{ }^\circ\text{C}$ | Ch-1 | | | 40 | A | |
| | | | Ch-2 | | | 40 | | |
| Pulse Diode Forward Current ^a | I_{SM} | | Ch-1 | | | 100 | | |
| | | | Ch-2 | | | 120 | | |
| Body Diode Voltage | V_{SD} | $I_S = 10\text{ A}$, $V_{GS} = 0\text{ V}$ | Ch-1 | | 0.8 | 1.2 | V | |
| | | $I_S = 10\text{ A}$, $V_{GS} = 0\text{ V}$ | Ch-2 | | 0.8 | 1.2 | | |
| Body Diode Reverse Recovery Time | t_{rr} | Channel-1 $I_F = 10\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25\text{ }^\circ\text{C}$ | Ch-1 | | 26 | 50 | ns | |
| | | | Ch-2 | | 36 | 70 | | |
| Body Diode Reverse Recovery Charge | Q_{rr} | | Channel-2 $I_F = 10\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25\text{ }^\circ\text{C}$ | Ch-1 | | 25 | 50 | nC |
| | | | | Ch-2 | | 36 | 70 | |
| Reverse Recovery Fall Time | t_a | | Ch-1 | | 17 | | ns | |
| | | | Ch-2 | | 20 | | | |
| Reverse Recovery Rise Time | t_b | | Ch-1 | | 9 | | | |
| | | | Ch-2 | | 16 | | | |

Notes:

- a. Guaranteed by design, not subject to production testing.
 b. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

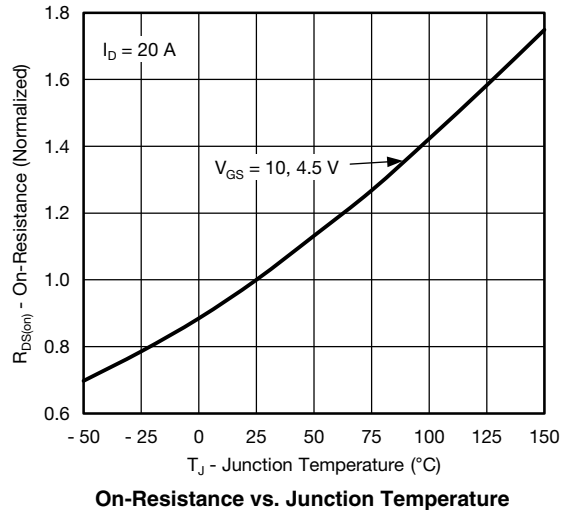
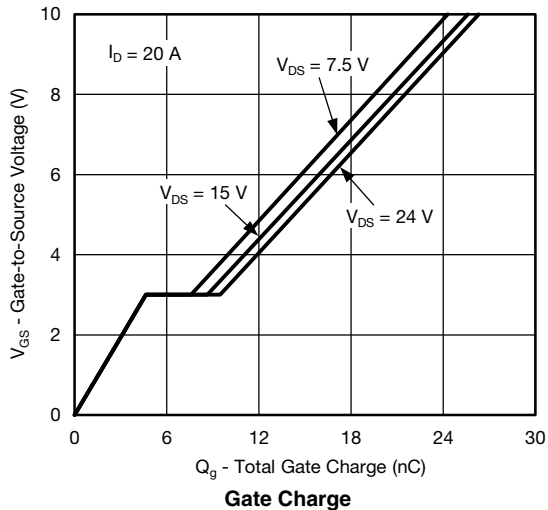
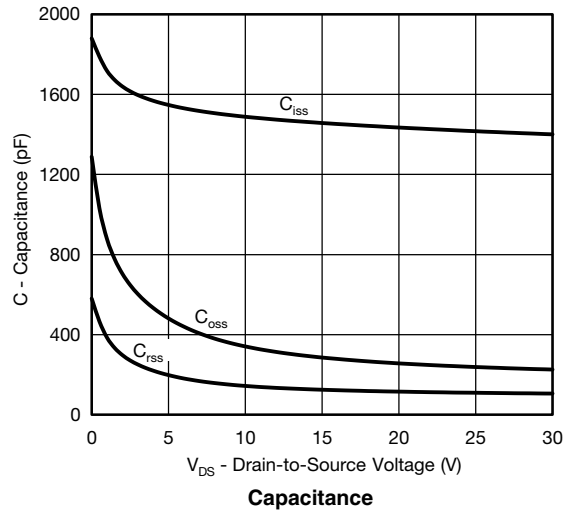
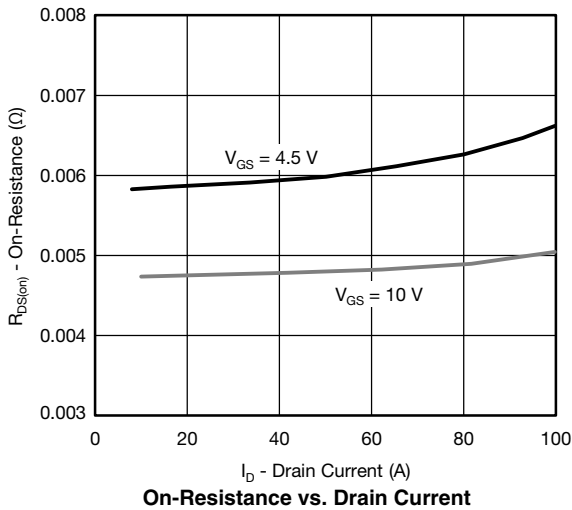
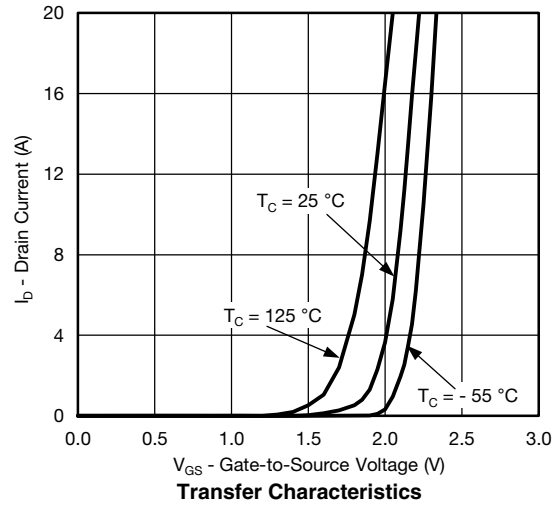
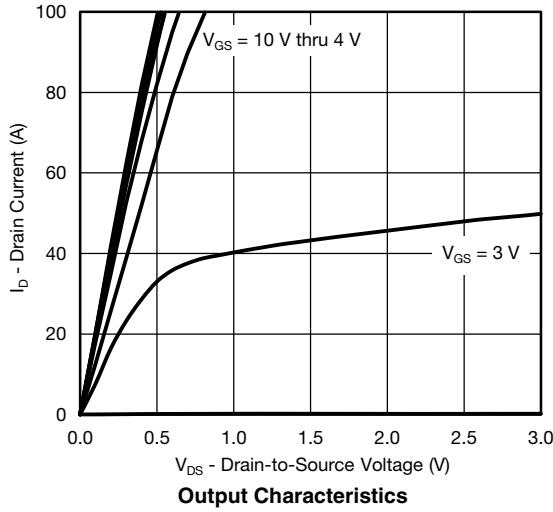
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

SiZ910DT

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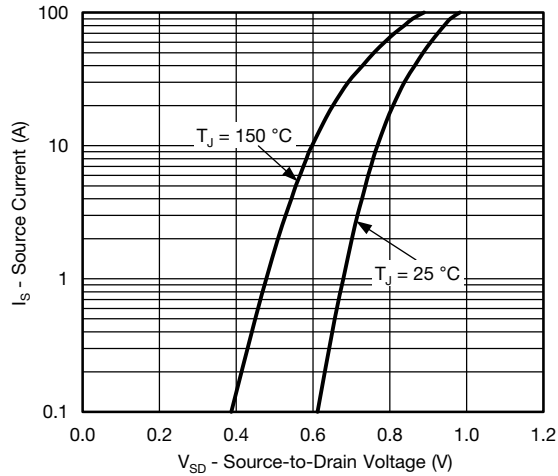


CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

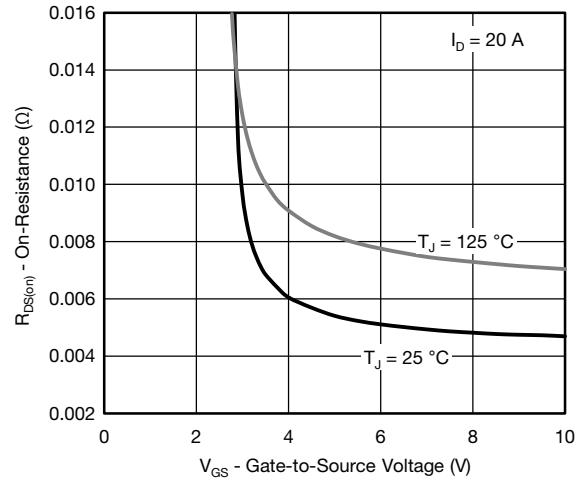




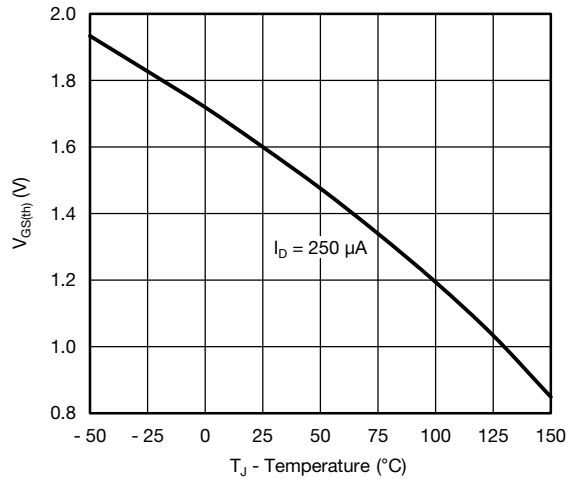
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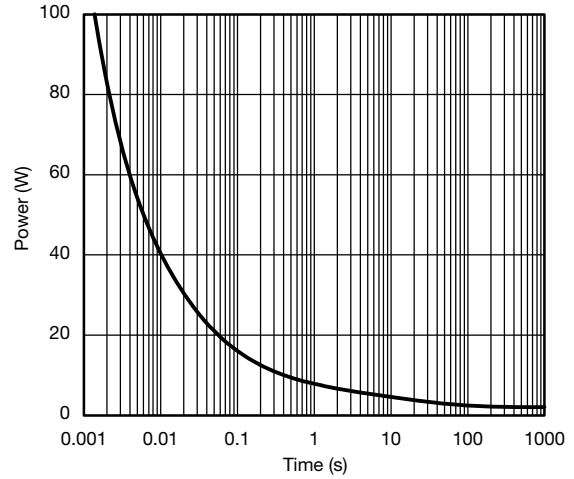
Source-Drain Diode Forward Voltage



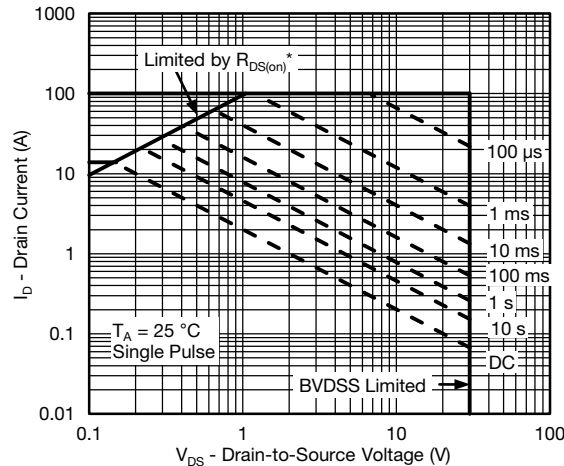
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power



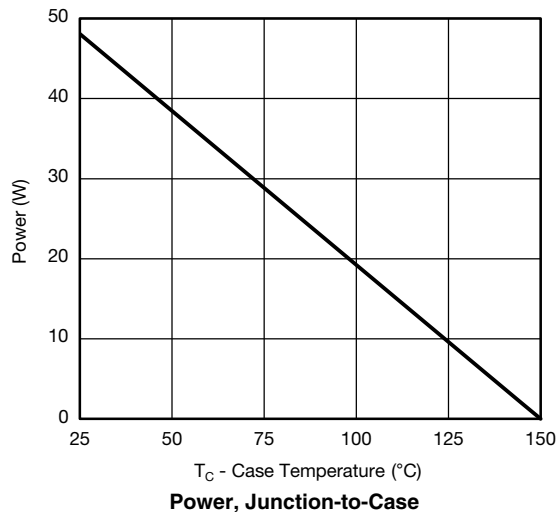
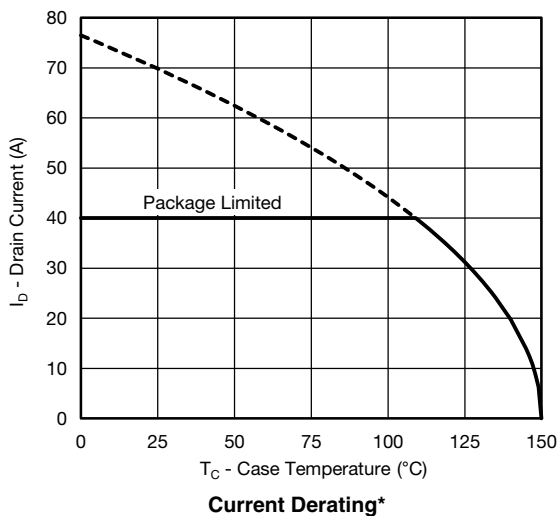
Safe Operating Area, Junction-to-Ambient

SiZ910DT

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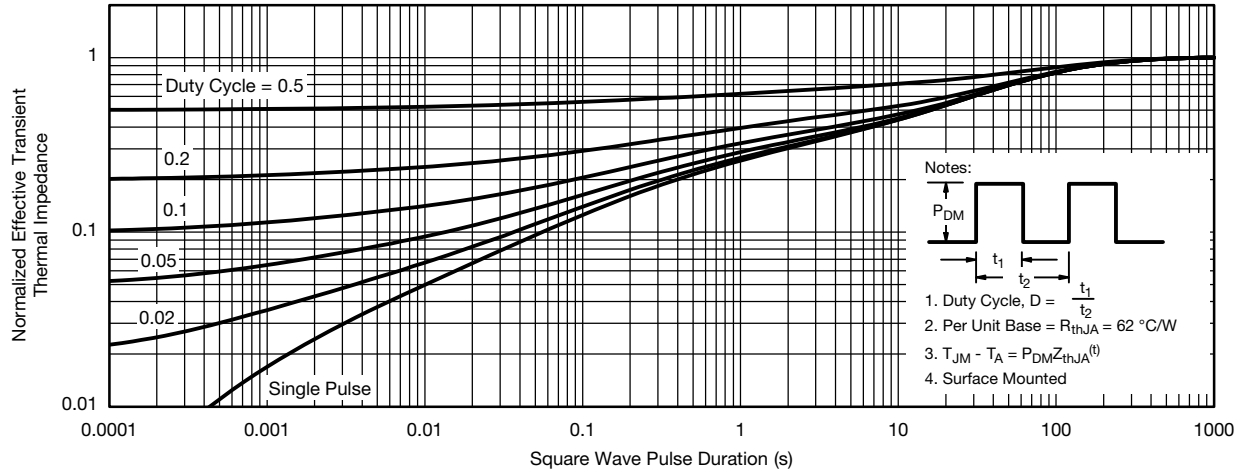
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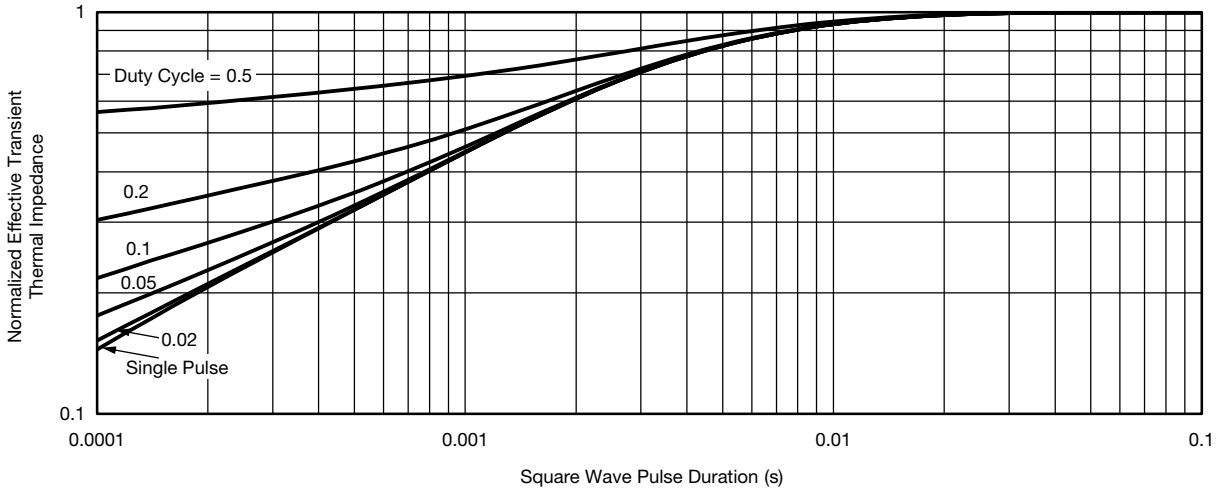
* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



CHANNEL-1 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



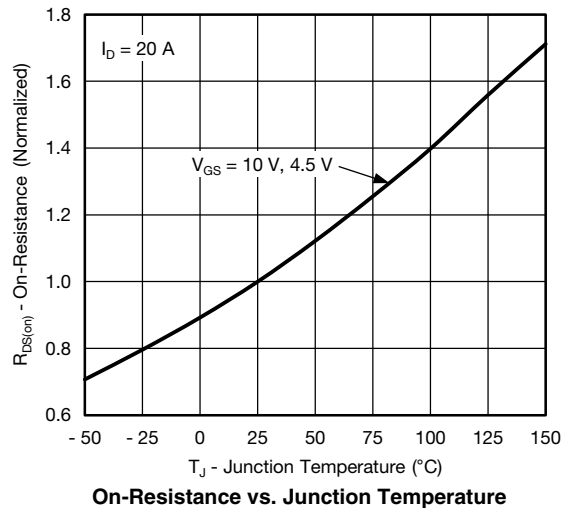
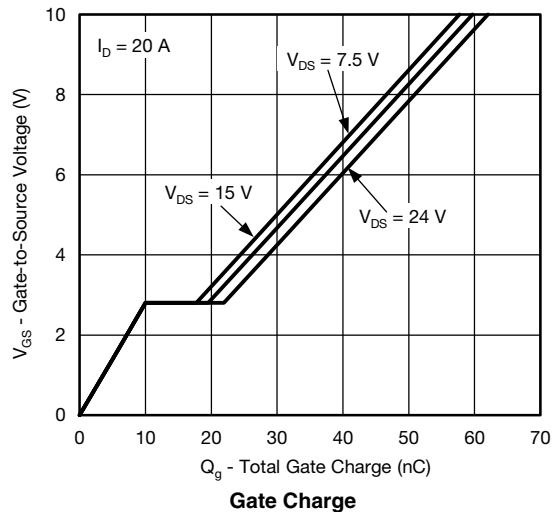
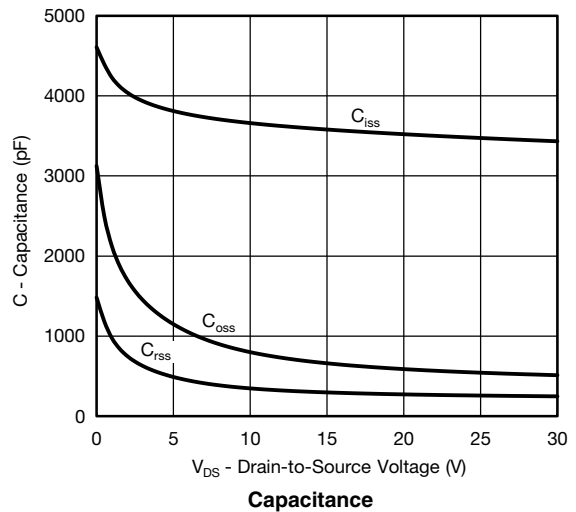
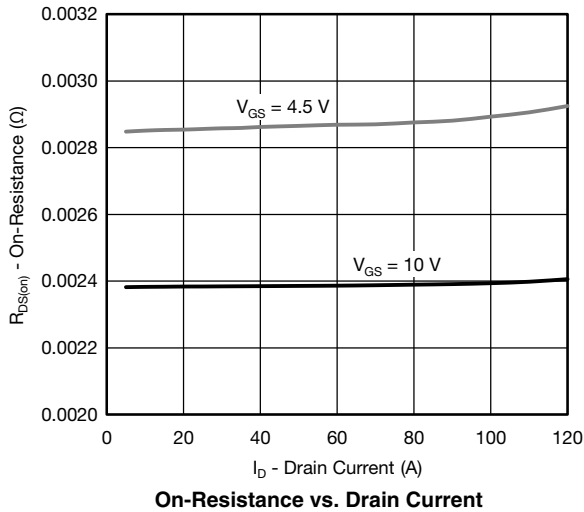
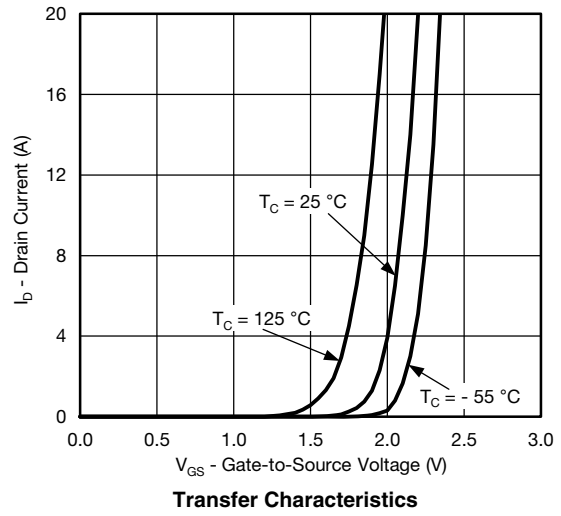
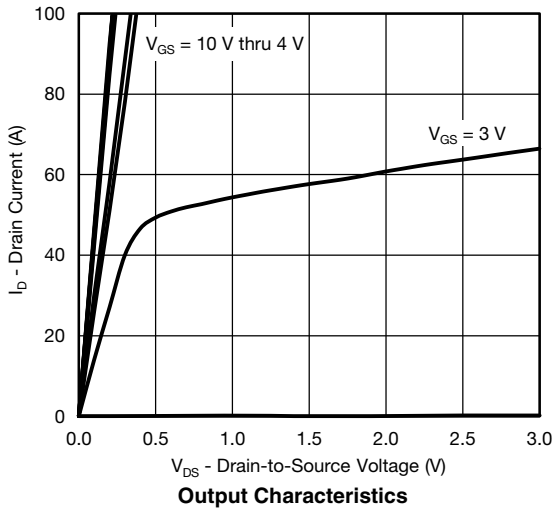
Normalized Thermal Transient Impedance, Junction-to-Case

SiZ910DT

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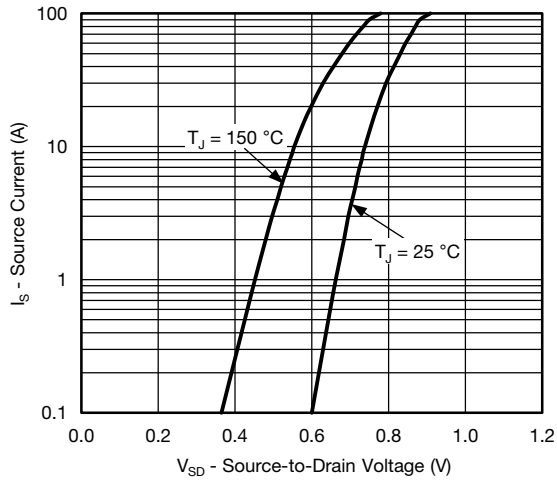


CHANNEL-2 TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

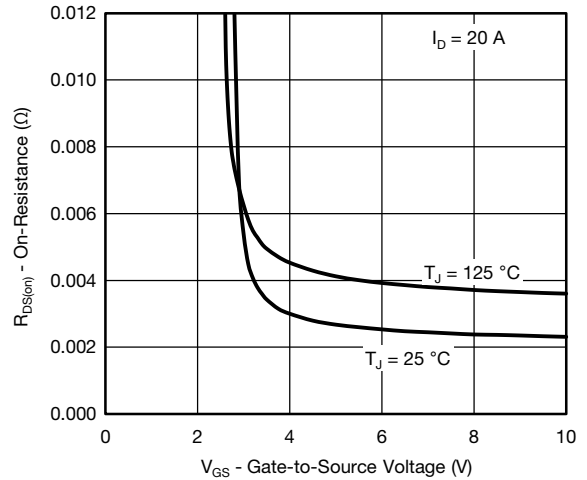




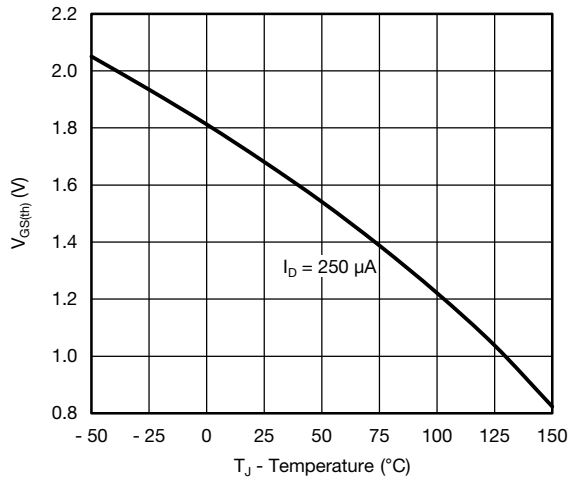
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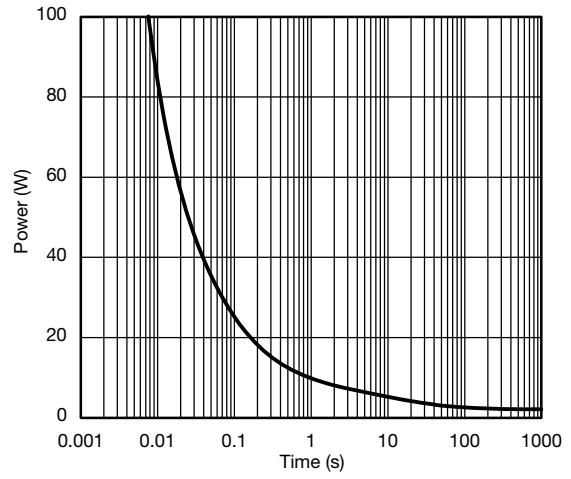
Source-Drain Diode Forward Voltage



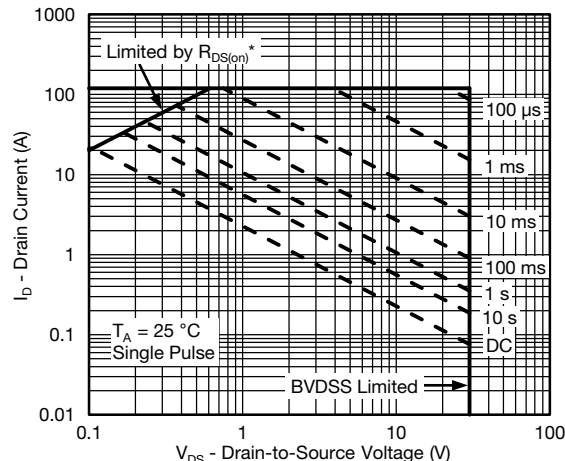
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



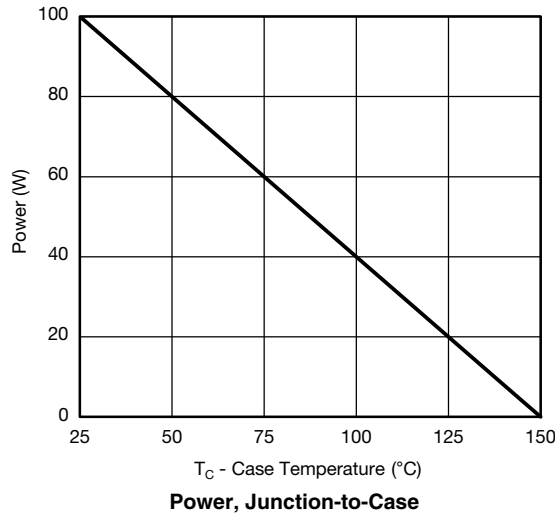
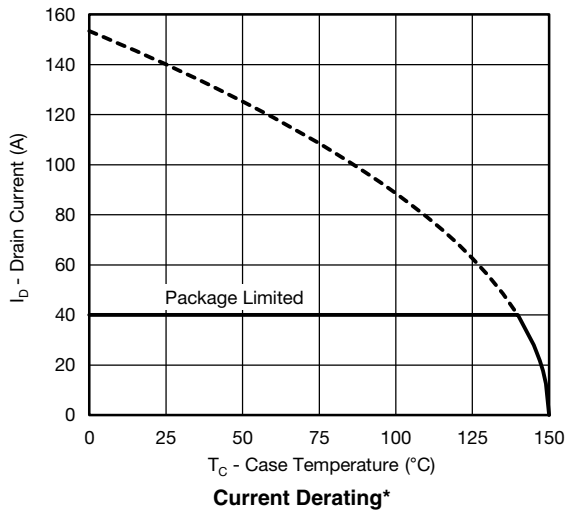
Single Pulse Power



Safe Operating Area, Junction-to-Ambient



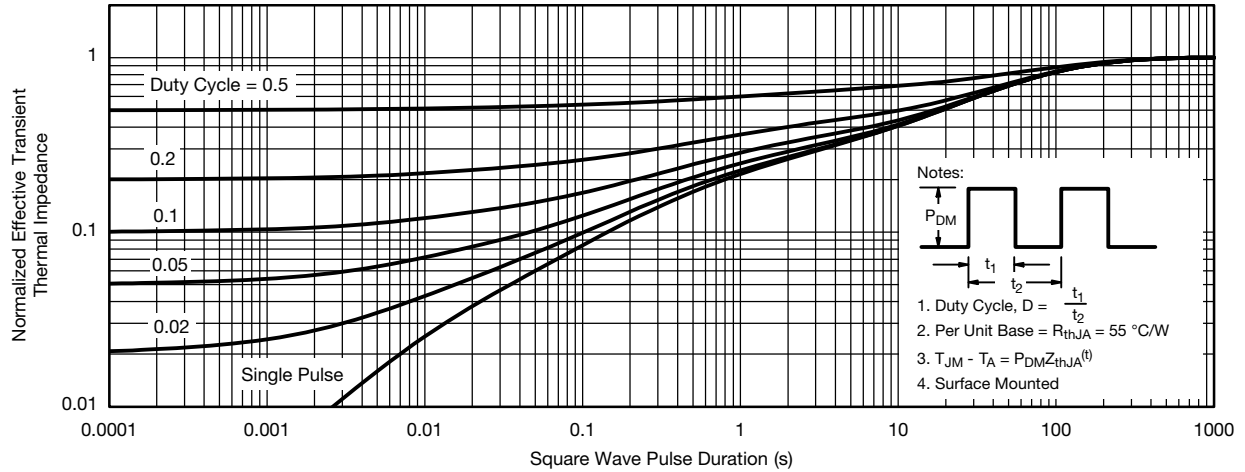
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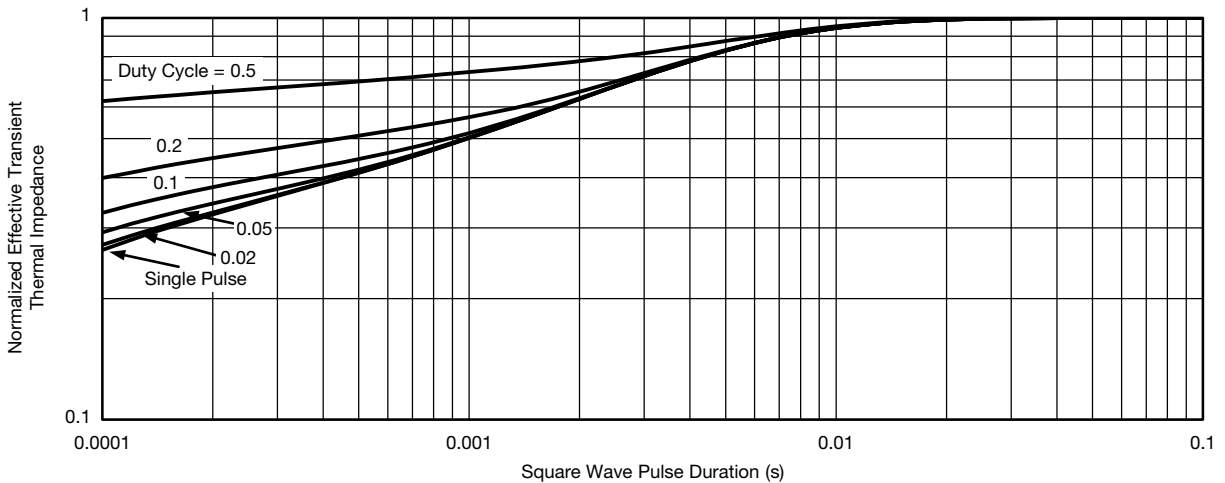
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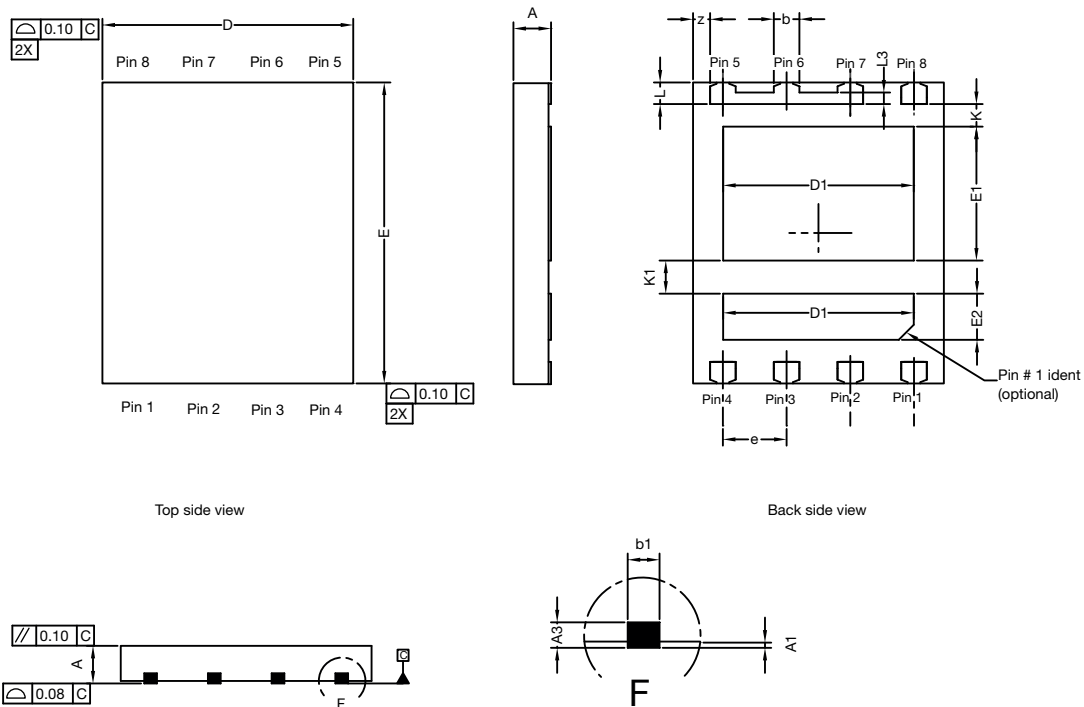
Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63539.

PowerPAIR® 6 x 5 Case Outline



Top side view

Back side view

| DIM. | MILLIMETERS | | | INCHES | | |
|---------------------------------|-------------|------|------|------------|-------|-------|
| | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. |
| A | 0.70 | 0.75 | 0.80 | 0.028 | 0.030 | 0.032 |
| A1 | 0.00 | - | 0.10 | 0.000 | - | 0.004 |
| A3 | 0.15 | 0.20 | 0.25 | 0.006 | 0.007 | 0.009 |
| b | 0.43 | 0.51 | 0.61 | 0.017 | 0.020 | 0.024 |
| b1 | 0.25 BSC | | | 0.010 BSC | | |
| D | 4.90 | 5.00 | 5.10 | 0.192 | 0.196 | 0.200 |
| D1 | 3.75 | 3.80 | 3.85 | 0.148 | 0.150 | 0.152 |
| E | 5.90 | 6.00 | 6.10 | 0.232 | 0.236 | 0.240 |
| E1 Option AA (for W/B) | 2.62 | 2.67 | 2.72 | 0.103 | 0.105 | 0.107 |
| E1 Option AB (for BWL) | 2.42 | 2.47 | 2.52 | 0.095 | 0.097 | 0.099 |
| E2 | 0.87 | 0.92 | 0.97 | 0.034 | 0.036 | 0.038 |
| e | 1.27 BSC | | | 0.050 BSC | | |
| K Option AA (for W/B) | 0.45 typ. | | | 0.018 typ. | | |
| K Option AB (for BWL) | 0.65 typ. | | | 0.025 typ. | | |
| K1 | 0.66 typ. | | | 0.025 typ. | | |
| L | 0.33 | 0.43 | 0.53 | 0.013 | 0.017 | 0.020 |
| L3 | 0.23 BSC | | | 0.009 BSC | | |
| z | 0.34 BSC | | | 0.013 BSC | | |
| ECN: T14-0782-Rev. C, 22-Dec-14 | | | | | | |
| DWG: 6005 | | | | | | |

Recommended Minimum PAD for PowerPAIR® 6 x 5



Dimensions in millimeters (inch)

Note

- Linear dimensions are in black, the same information is provided in ordinate dimensions which are in blue.



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